

Dual N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ)
60	1.4 at $V_{GS} = 10$ V	0.37	0.47
	3.0 at $V_{GS} = 4.5$ V	0.25	

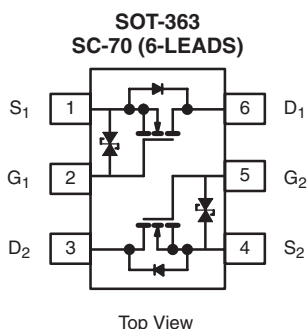
FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g Tested
- ESD Protected: 1800 V

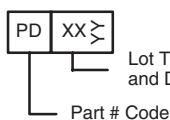
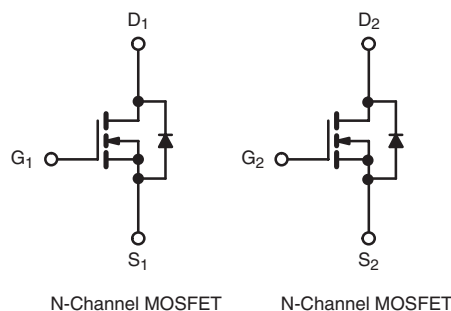

RoHS
COMPLIANT

APPLICATIONS

- Low Power Load Switch



Marking Code


Ordering Information: Si1926DL-T1-E3 (Lead (Pb)-free)


ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	0.37	A
	$T_C = 70$ °C	0.30	
	$T_A = 25$ °C	0.34 ^{b, c}	
	$T_A = 70$ °C	0.27 ^{b, c}	
Pulsed Drain Current	I_{DM}	0.65	A
Continuous Source-Drain Diode Current	$T_C = 25$ °C	0.43	
	$T_A = 25$ °C	0.25 ^{b, c}	
Maximum Power Dissipation	$T_C = 25$ °C	0.51	W
	$T_C = 70$ °C	0.33	
	$T_A = 25$ °C	0.30 ^{b, c}	
	$T_A = 70$ °C	0.20 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	360	415	°C/W
Maximum Junction-to-Foot (Drain)	R_{thJF}	300	350	

Notes:

- Based on $T_C = 25$ °C.
- Surface mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- Maximum under Steady State conditions is 400 °C/W.

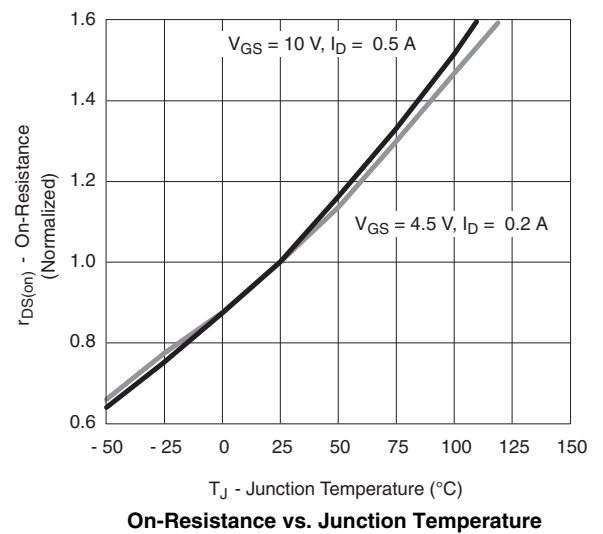
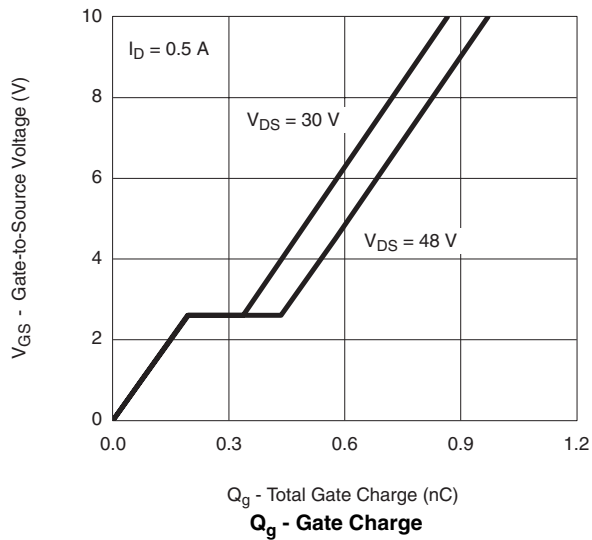
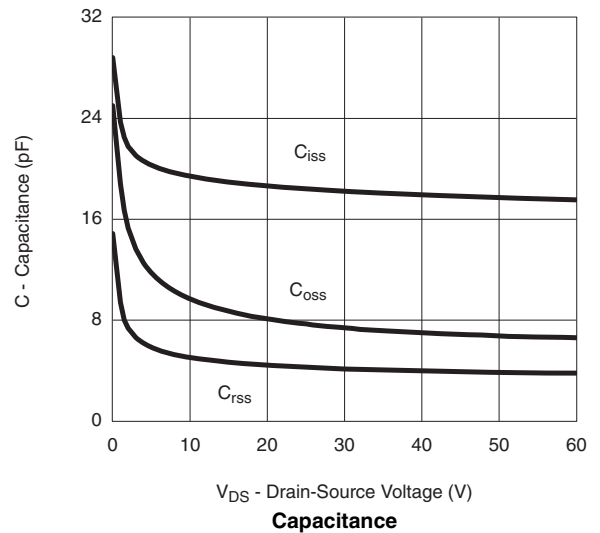
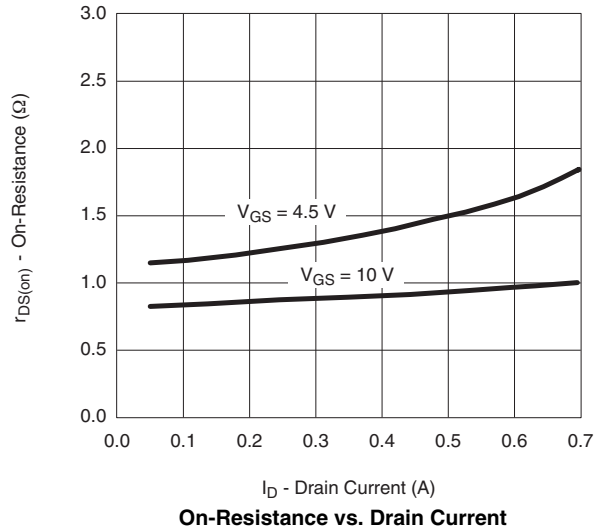
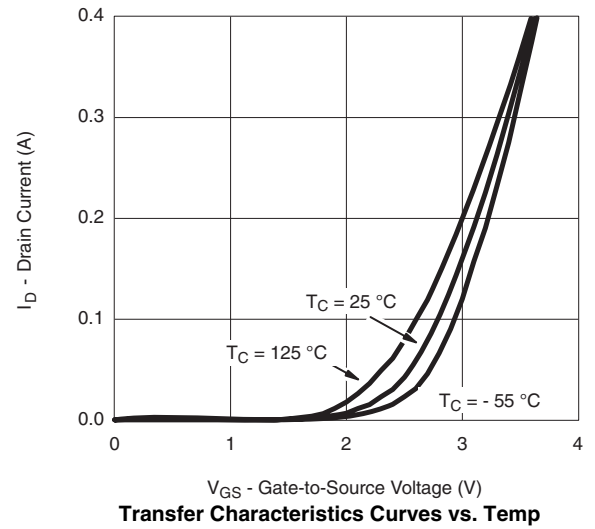
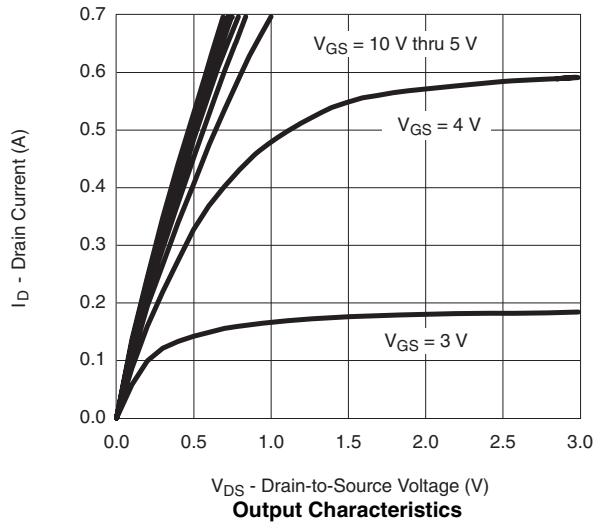
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	60			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		56.7		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 3		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1		2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 10 V			± 150	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			10	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 85 °C			100	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 4.5 V	0.50			A
		V _{DS} ≥ 7.5 V, V _{GS} = 10 V	0.65			
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 0.34			1.4	Ω
		V _{GS} = 4.5 V, I _D = 0.23			3	
Forward Transconductance	g _{fs}	V _{DS} = 30 V, I _D = 0.2 A		159		ms
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz		18.5		pF
Output Capacitance	C _{oss}			7.5		
Reverse Transfer Capacitance	C _{rss}			4.2		
Total Gate Charge	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 0.34		0.9	1.4	nC
		V _{DS} = 30 V, V _{GS} = 4.5 V, I _D = 0.34		0.5	0.75	
Gate-Source Charge	Q _{gs}			0.2		
Gate-Drain Charge	Q _{gd}			0.15		
Gate Resistance	R _g	f = 1 MHz		160	240	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 30 V, R _L = 100 Ω I _D ≅ 0.3 A, V _{GEN} = 10 V, R _g = 1 Ω		6.5	10	ns
Rise Time	t _r			12	18	
Turn-Off DelayTime	t _{d(off)}			13	22	
Fall Time	t _f			14	21	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			0.43	A
Pulse Diode Forward Current ^a	I _{SM}				0.65	
Body Diode Voltage	V _{SD}	I _S = 0.3 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 0.6 A, di/dt = 100 A/μs		16.5	25	nC
Body Diode Reverse Recovery Charge	Q _{rr}			13	20	ns
Reverse Recovery Fall Time	t _a			13.5		
Reverse Recovery Rise Time	t _b			3		

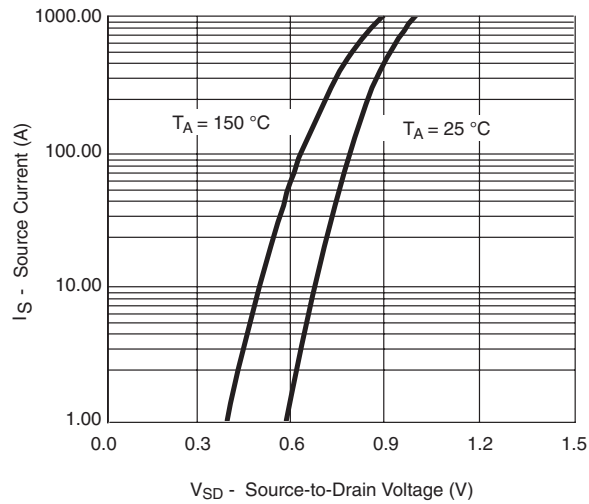
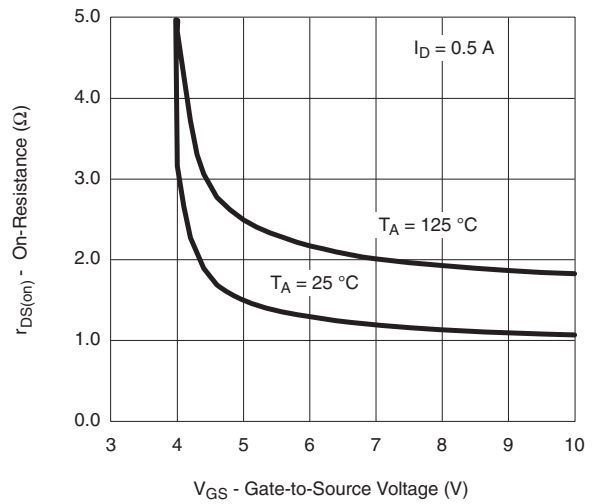
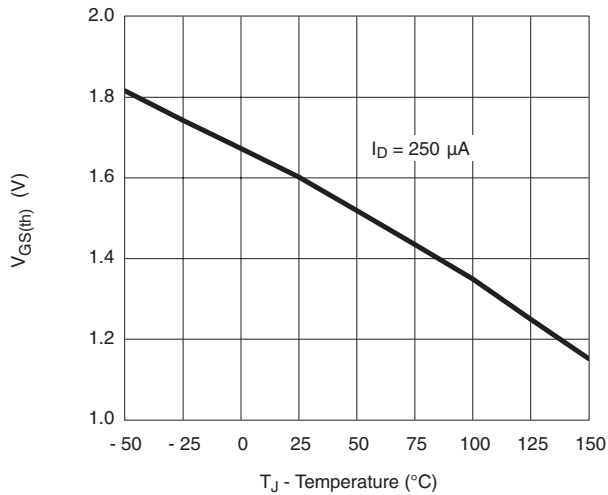
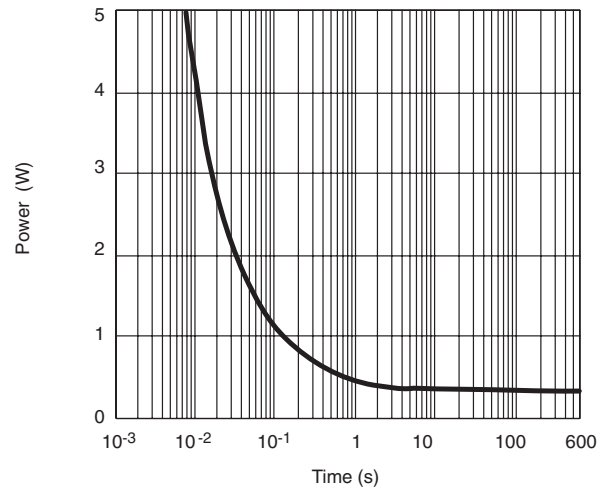
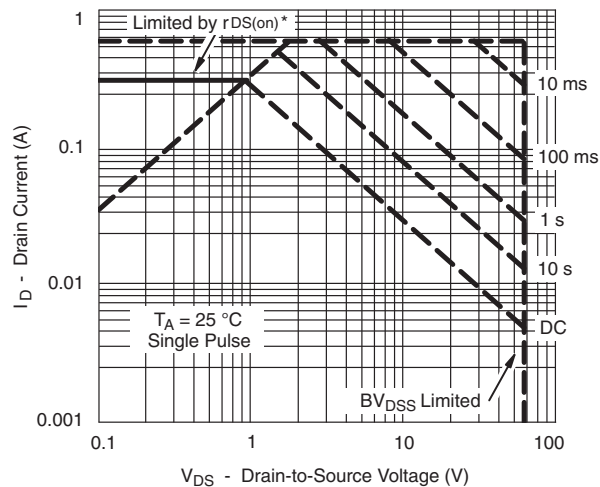
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

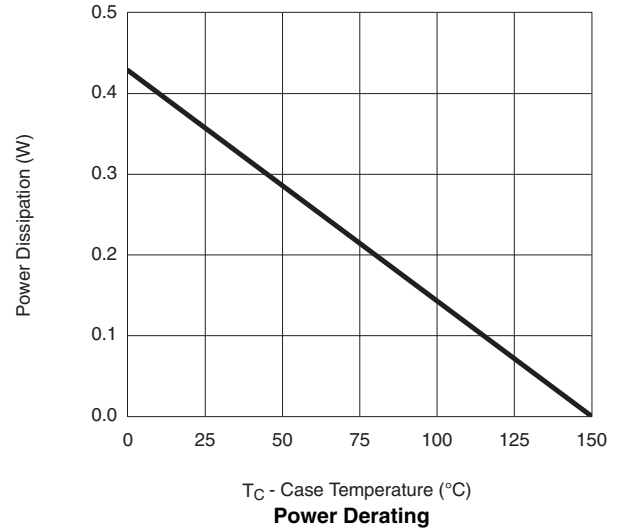
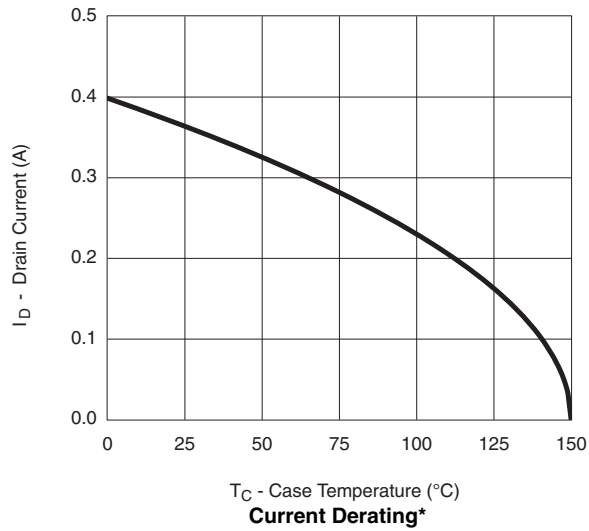
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

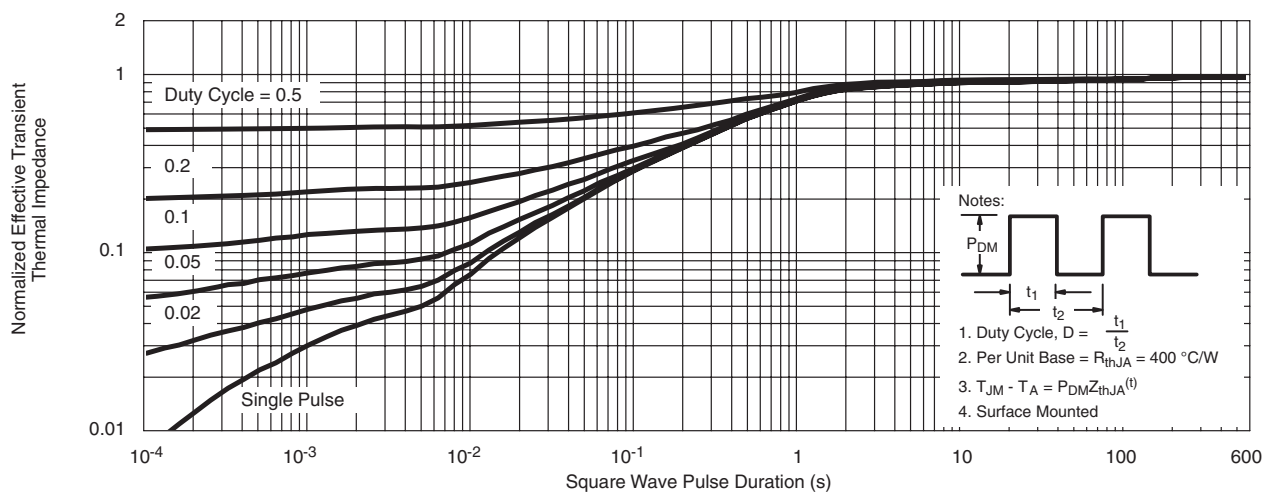
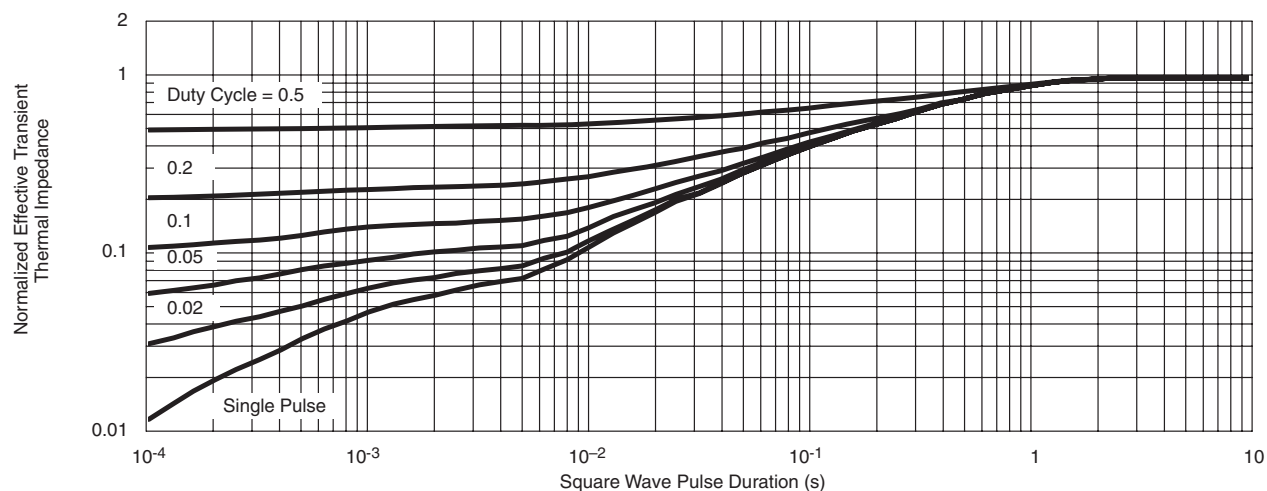
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage** **$r_{DS(on)}$ vs. V_{GS} vs. Temperature****Threshold Voltage****Single Pulse Power****Safe Operating Area**



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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